



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

8050SS TRANSISTOR (NPN)**FEATURES**

Power dissipation

 P_{CM} : 1 W (Tamb=25)

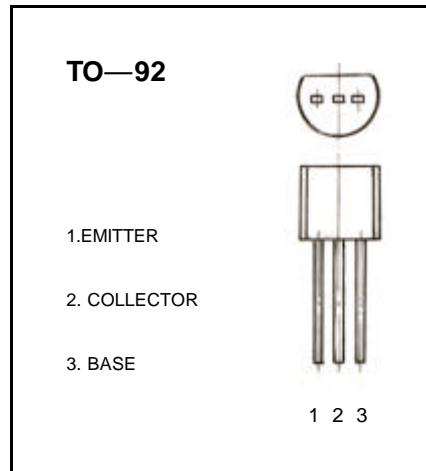
Collector current

 I_{CM} : 1.5 A

Collector-base voltage

 $V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150**ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)**

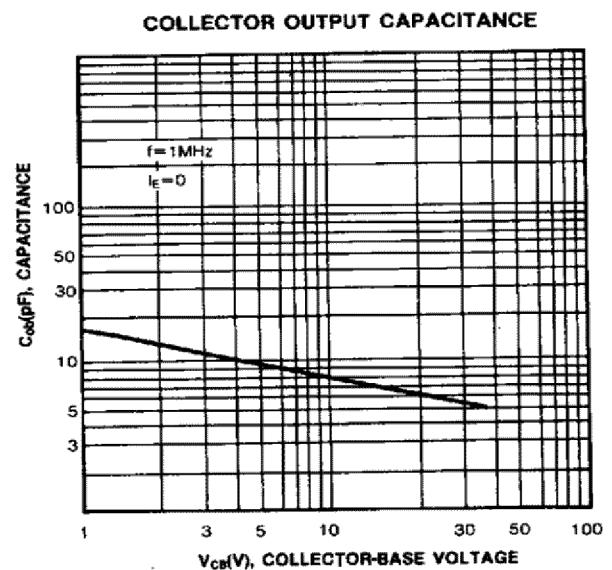
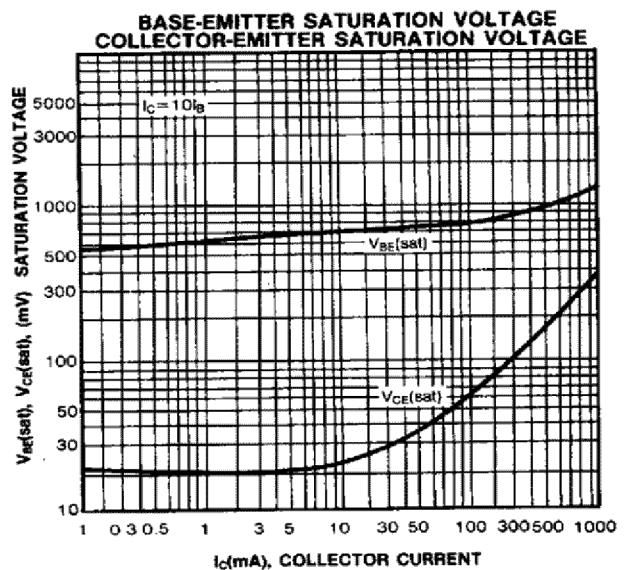
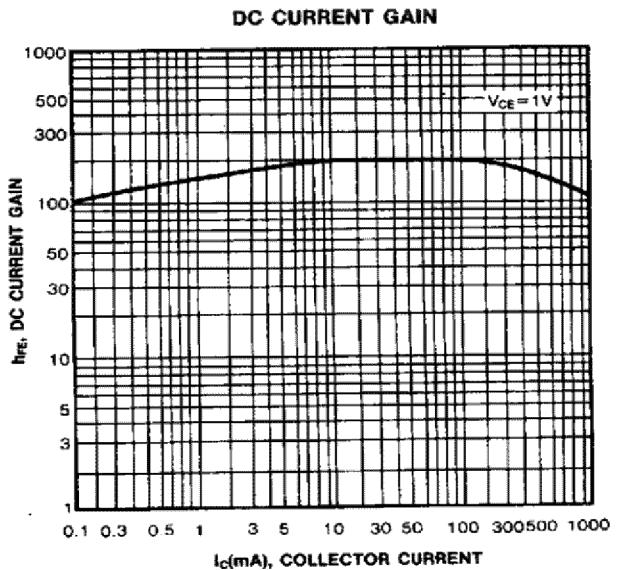
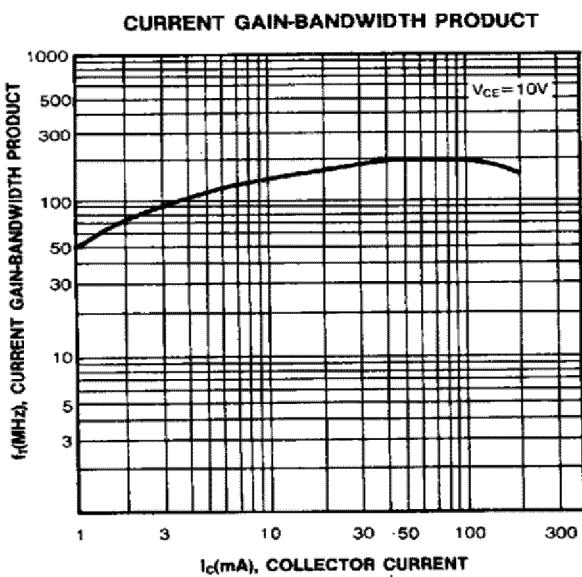
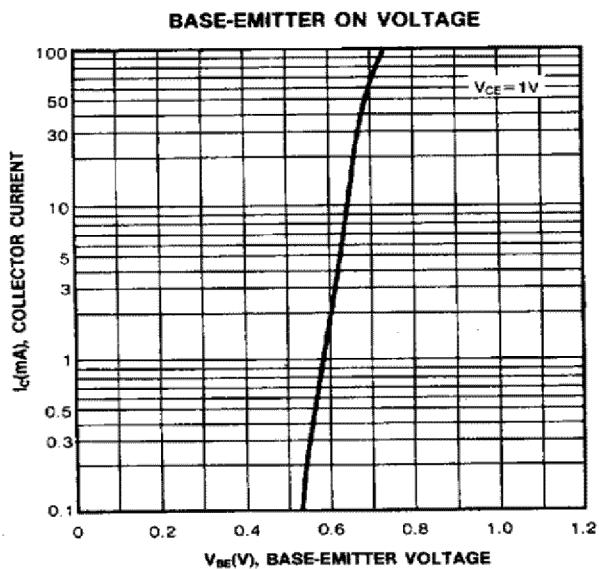
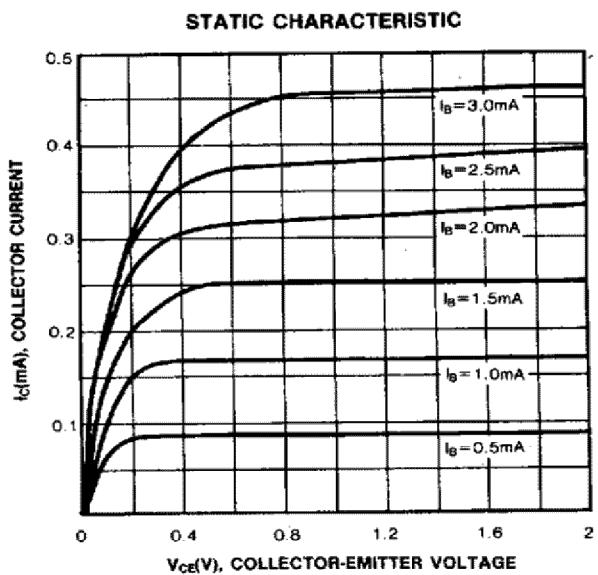
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1 mA, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40 V, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20 V, I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1 V, I_C = 100 mA$	85		300	
	$h_{FE(2)}$	$V_{CE} = 1 V, I_C = 800 mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800 mA, I_B = 80 mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800mA, I_B = 80 mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 10 V, I_B = 50mA$ $f = 30 MHz$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

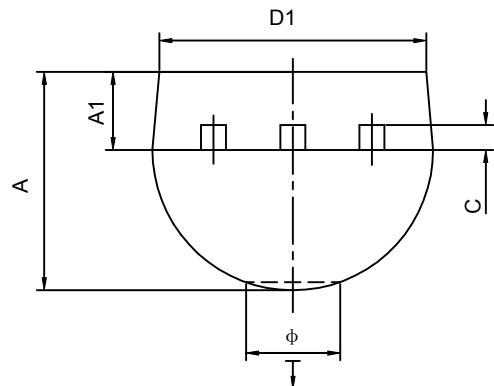
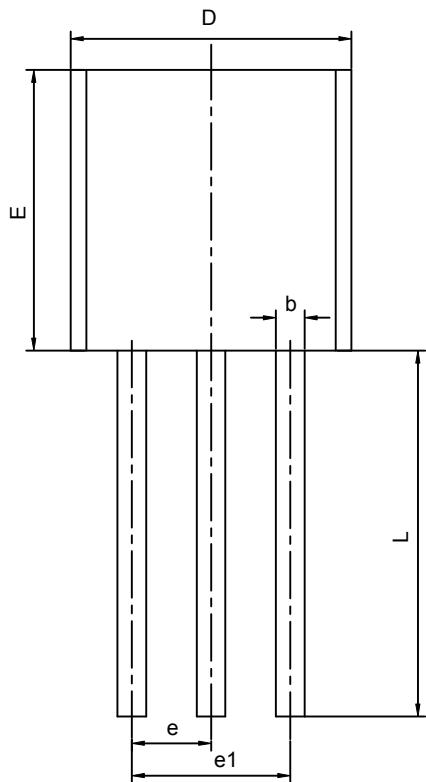
Rank	B	C	D
Range	85-160	120-200	160-300

Typical Characteristics

8050SS



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
↓	0.000	0.380	0.000	0.015